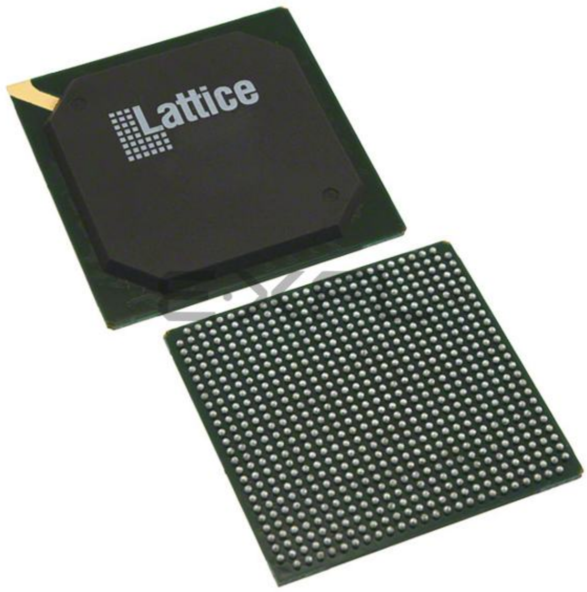
Lattice Semiconductor Corporation - LFE3-35EA-6LFN672I Datasheet



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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	4125
Number of Logic Elements/Cells	33000
Total RAM Bits	1358848
Number of I/O	310
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-35ea-6lfn672i

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LatticeECP3 Family Data Sheet
Architecture

June 2013 **Data Sheet DS1021**

Architecture Overview

Each LatticeECP3 device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM™ Embedded Block RAM (EBR) and rows of sysDSP™ Digital Signal Processing slices, as shown in Figure 2-1. The LatticeECP3-150 has four rows of DSP slices; all other LatticeECP3 devices have two rows of DSP slices. In addition, the LatticeECP3 family contains SERDES Quads on the bottom of the device.

There are two kinds of logic blocks, the Programmable Functional Unit (PFU) and Programmable Functional Unit without RAM (PFF). The PFU contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFF block contains building blocks for logic, arithmetic and ROM functions. Both PFU and PFF blocks are optimized for flexibility, allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array. Only one type of block is used per row.

The LatticeECP3 devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large, dedicated 18Kbit fast memory blocks. Each sysMEM block can be configured in a variety of depths and widths as RAM or ROM. In addition, LatticeECP3 devices contain up to two rows of DSP slices. Each DSP slice has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

The LatticeECP3 devices feature up to 16 embedded 3.2 Gbps SERDES (Serializer / Deserializer) channels. Each SERDES channel contains independent 8b/10b encoding / decoding, polarity adjust and elastic buffer logic. Each group of four SERDES channels, along with its Physical Coding Sub-layer (PCS) block, creates a quad. The functionality of the SERDES/PCS quads can be controlled by memory cells set during device configuration or by registers that are addressable during device operation. The registers in every quad can be programmed via the SERDES Client Interface (SCI). These quads (up to four) are located at the bottom of the devices.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysI/O buffers. The sysI/O buffers of the LatticeECP3 devices are arranged in seven banks, allowing the implementation of a wide variety of I/O standards. In addition, a separate I/O bank is provided for the programming interfaces. 50% of the PIO pairs on the left and right edges of the device can be configured as LVDS transmit/receive pairs. The PIC logic also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as XGMII, 7:1 LVDS, along with memory interfaces including DDR3.

The LatticeECP3 registers in PFU and sysI/O can be configured to be SET or RESET. After power up and the device is configured, it enters into user mode with these registers SET/RESET according to the configuration setting, allowing the device entering to a known state for predictable system function.

Other blocks provided include PLLs, DLLs and configuration functions. The LatticeECP3 architecture provides two Delay Locked Loops (DLLs) and up to ten Phase Locked Loops (PLLs). The PLL and DLL blocks are located at the end of the EBR/DSP rows.

The configuration block that supports features such as configuration bit-stream decryption, transparent updates and dual-boot support is located toward the center of this EBR row. Every device in the LatticeECP3 family supports a sysCONFIG™ port located in the corner between banks one and two, which allows for serial or parallel device configuration.

In addition, every device in the family has a JTAG port. This family also provides an on-chip oscillator and soft error detect capability. The LatticeECP3 devices use 1.2 V as their core voltage.

Figure 2-4. General Purpose PLL Diagram

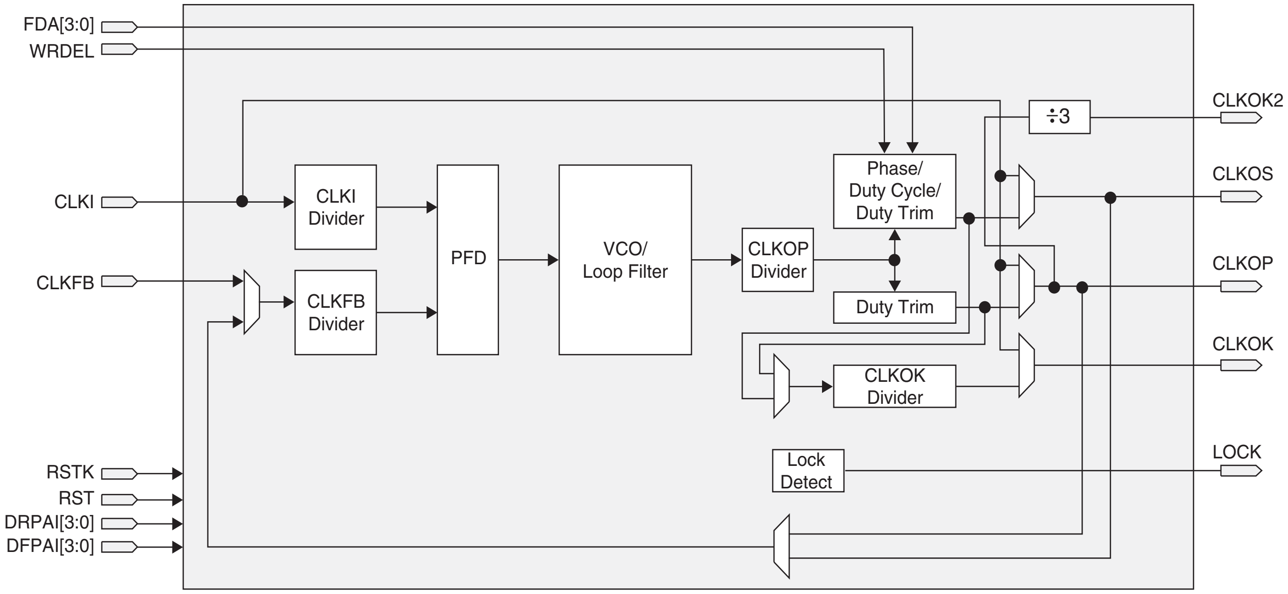


Table 2-4 provides a description of the signals in the PLL blocks.

Table 2-4. PLL Blocks Signal Descriptions

Signal	I/O	Description
CLKI	I	Clock input from external pin or routing
CLKFB	I	PLL feedback input from CLKOP, CLKOS, or from a user clock (pin or logic)
RST	I	"1" to reset PLL counters, VCO, charge pumps and M-dividers
RSTK	I	"1" to reset K-divider
WRDEL	I	DPA Fine Delay Adjust input
CLKOS	O	PLL output to clock tree (phase shifted/duty cycle changed)
CLKOP	O	PLL output to clock tree (no phase shift)
CLKOK	O	PLL output to clock tree through secondary clock divider
CLKOK2	O	PLL output to clock tree (CLKOP divided by 3)
LOCK	O	"1" indicates PLL LOCK to CLKI
FDA [3:0]	I	Dynamic fine delay adjustment on CLKOS output
DRPAI[3:0]	I	Dynamic coarse phase shift, rising edge setting
DFPAI[3:0]	I	Dynamic coarse phase shift, falling edge setting

Delay Locked Loops (DLL)

In addition to PLLs, the LatticeECP3 family of devices has two DLLs per device.

CLKI is the input frequency (generated either from the pin or routing) for the DLL. CLKI feeds into the output muxes block to bypass the DLL, directly to the DELAY CHAIN block and (directly or through divider circuit) to the reference input of the Phase Detector (PD) input mux. The reference signal for the PD can also be generated from the Delay Chain signals. The feedback input to the PD is generated from the CLKFB pin or from a tapped signal from the Delay chain.

The PD produces a binary number proportional to the phase and frequency difference between the reference and feedback signals. Based on these inputs, the ALU determines the correct digital control codes to send to the delay

The edge clocks on the top, left, and right sides of the device can drive the secondary clocks or general routing resources of the device. The left and right side edge clocks also can drive the primary clock network through the clock dividers (CLKDIV).

sysMEM Memory

LatticeECP3 devices contain a number of sysMEM Embedded Block RAM (EBR). The EBR consists of an 18-Kbit RAM with memory core, dedicated input registers and output registers with separate clock and clock enable. Each EBR includes functionality to support true dual-port, pseudo dual-port, single-port RAM, ROM and FIFO buffers (via external PFUs).

sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-7. FIFOs can be implemented in sysMEM EBR blocks by implementing support logic with PFUs. The EBR block facilitates parity checking by supporting an optional parity bit for each data byte. EBR blocks provide byte-enable support for configurations with18-bit and 36-bit data widths. For more information, please see TN1179, LatticeECP3 Memory Usage Guide.

Table 2-7. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Memory Cascading

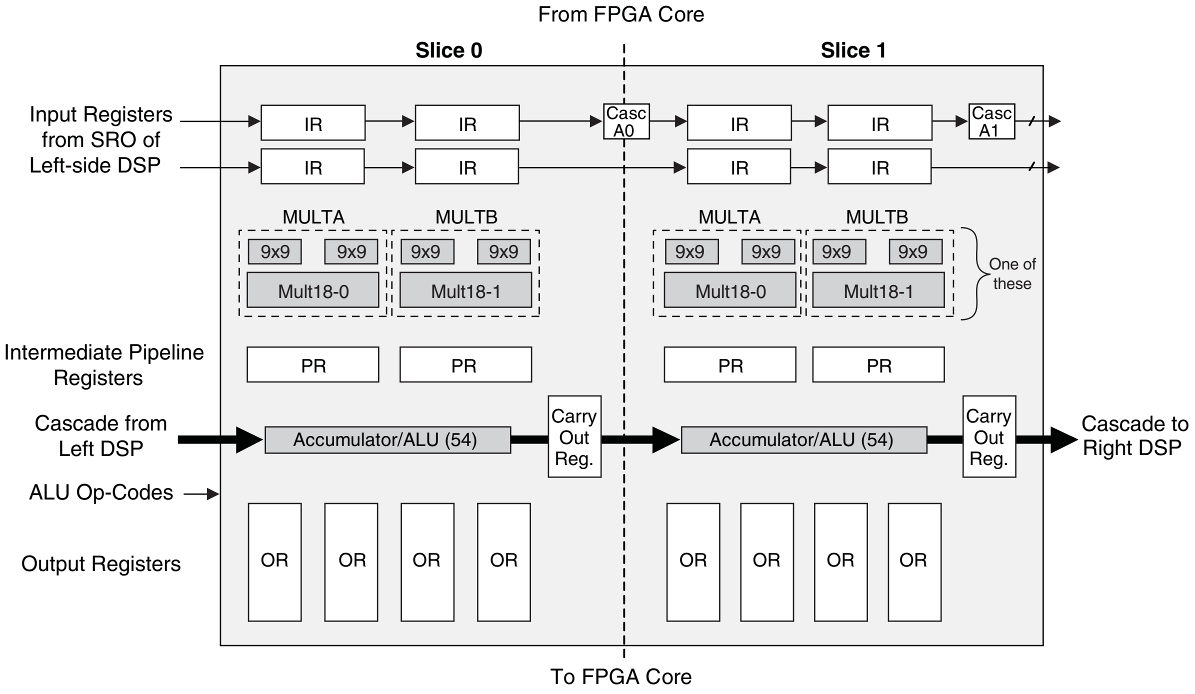
Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

as, overflow, underflow and convergent rounding, etc.
  - Flexible cascading across slices to get larger functions

- RTL Synthesis friendly synchronous reset on all registers, while still supporting asynchronous reset for legacy users
- Dynamic MUX selection to allow Time Division Multiplexing (TDM) of resources for applications that require processor-like flexibility that enables different functions for each clock cycle

For most cases, as shown in Figure 2-24, the LatticeECP3 DSP slice is backwards-compatible with the LatticeECP2™ sysDSP block, such that, legacy applications can be targeted to the LatticeECP3 sysDSP slice. The functionality of one LatticeECP2 sysDSP Block can be mapped into two adjacent LatticeECP3 sysDSP slices, as shown in Figure 2-25.

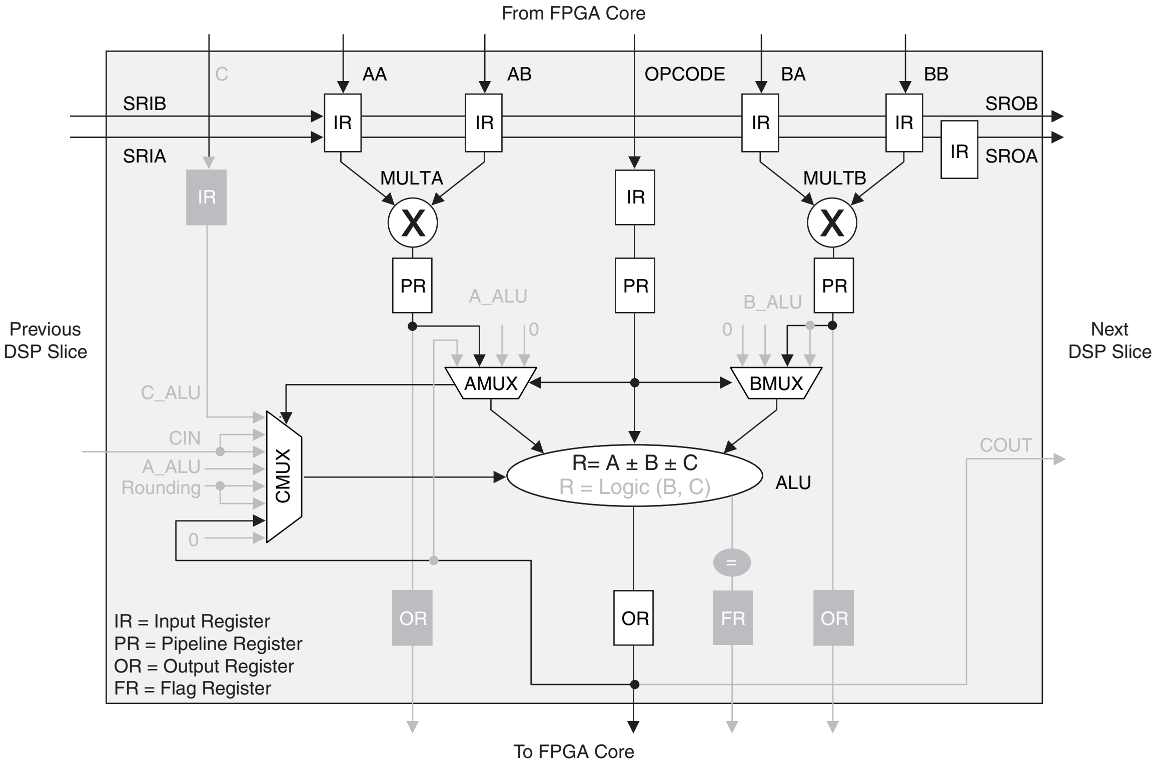
Figure 2-24. Simplified sysDSP Slice Block Diagram



MMAC DSP Element

The LatticeECP3 supports a MAC with two multipliers. This is called Multiply Multiply Accumulate or MMAC. In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value and with the result of the multiplier operation of operands BA and BB. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-28 shows the MMAC sysDSP element.

Figure 2-28. MMAC sysDSP Element



Two adjacent PIOs can be joined to provide a differential I/O pair (labeled as "T" and "C") as shown in Figure 2-32. The PAD Labels "T" and "C" distinguish the two PIOs. Approximately 50% of the PIO pairs on the left and right edges of the device can be configured as true LVDS outputs. All I/O pairs can operate as LVDS inputs.

Table 2-11. PIO Signal List

Name	Type	Description
INDD	Input Data	Register bypassed input. This is not the same port as INCK.
IPA, INA, IPB, INB	Input Data	Ports to core for input data
OPOSA, ONEGA[1], OPOSB, ONEGB[1]	Output Data	Output signals from core. An exception is the ONEGB port, used for tristate logic at the DQS pad.
CE	PIO Control	Clock enables for input and output block flip-flops.
SCLK	PIO Control	System Clock (PCLK) for input and output/TS blocks. Connected from clock ISB.
LSR	PIO Control	Local Set/Reset
ECLK1, ECLK2	PIO Control	Edge clock sources. Entire PIO selects one of two sources using mux.
ECLKDQSR[1]	Read Control	From DQS_STROBE, shifted strobe for memory interfaces only.
DDRCLKPOL[1]	Read Control	Ensures transfer from DQS domain to SCLK domain.
DDRLAT[1]	Read Control	Used to guarantee INDDRX2 gearing by selectively enabling a D-Flip-Flop in datapath.
DEL[3:0]	Read Control	Dynamic input delay control bits.
INCK	To Clock Distribution and PLL	PIO treated as clock PIO, path to distribute to primary clocks and PLL.
TS	Tristate Data	Tristate signal from core (SDR)
DQCLK0[1], DQCLK1[1]	Write Control	Two clocks edges, 90 degrees out of phase, used in output gearing.
DQSW[2]	Write Control	Used for output and tristate logic at DQS only.
DYNDEL[7:0]	Write Control	Shifting of write clocks for specific DQS group, using 6:0 each step is approximately 25ps, 128 steps. Bit 7 is an invert (timing depends on input frequency). There is also a static control for this 8-bit setting, enabled with a memory cell.
DCNTL[6:0]	PIO Control	Original delay code from DDR DLL
DATAVALID[1]	Output Data	Status flag from DATAVALID logic, used to indicate when input data is captured in IOLOGIC and valid to core.
READ	For DQS_Strobe	Read signal for DDR memory interface
DQSI	For DQS_Strobe	Unshifted DQS strobe from input pad
PRMBDET	For DQS_Strobe	DQSI biased to go high when DQSI is tristate, goes to input logic block as well as core logic.
GSRN	Control from routing	Global Set/Reset

1. Signals available on left/right/top edges only.
2. Selected PIO.

PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Input Register Block

The input register blocks for the PIOs, in the left, right and top edges, contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-33 shows the input register block for the left, right and top edges. The input register block for the bottom edge contains one element to register the input signal and no DDR registers. The following description applies to the input register block for PIOs in the left, right and top edges only.

DLL Calibrated DQS Delay Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces, a PLL is used for this adjustment. However, in DDR memories the clock (referred to as DQS) is not free-running so this approach cannot be used. The DQS Delay block provides the required clock alignment for DDR memory interfaces.

The delay required for the DQS signal is generated by two dedicated DLLs (DDR DLL) on opposite side of the device. Each DLL creates DQS delays in its half of the device as shown in Figure 2-36. The DDR DLL on the left side will generate delays for all the DQS Strobe pins on Banks 0, 7 and 6 and DDR DLL on the right will generate delays for all the DQS pins on Banks 1, 2 and 3. The DDR DLL loop compensates for temperature, voltage and process variations by using the system clock and DLL feedback loop. DDR DLL communicates the required delay to the DQS delay block using a 7-bit calibration bus (DCNTL[6:0])

The DQS signal (selected PIOs only, as shown in Figure 2-35) feeds from the PAD through a DQS control logic block to a dedicated DQS routing resource. The DQS control logic block consists of DQS Read Control logic block that generates control signals for the read side and DQS Write Control logic that generates the control signals required for the write side. A more detailed DQS control diagram is shown in Figure 2-37, which shows how the DQS control blocks interact with the data paths.

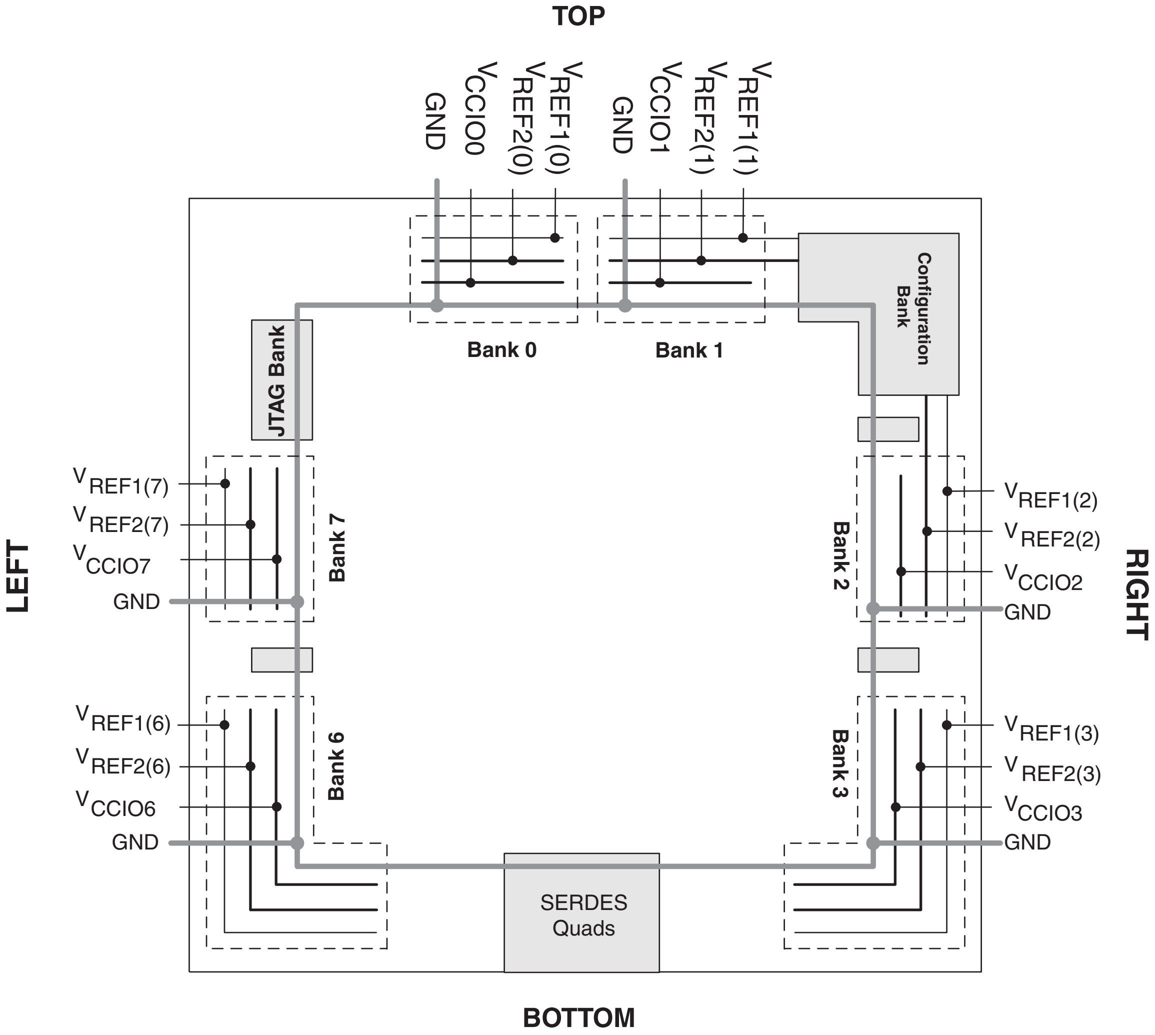
The DQS Read control logic receives the delay generated by the DDR DLL on its side and delays the incoming DQS signal by 90 degrees. This delayed ECLKDQSR is routed to 10 or 11 DQ pads covered by that DQS signal. This block also contains a polarity control logic that generates a DDRCLKPOL signal, which controls the polarity of the clock to the sync registers in the input register blocks. The DQS Read control logic also generates a DDRLAT signal that is in the input register block to transfer data from the first set of DDR register to the second set of DDR registers when using the DDRX2 gearbox mode for DDR3 memory interface.

The DQS Write control logic block generates the DQCLK0 and DQCLK1 clocks used to control the output gearing in the Output register block which generates the DDR data output and the DQS output. They are also used to control the generation of the DQS output through the DQS output register block. In addition to the DCNTL [6:0] input from the DDR DLL, the DQS Write control block also uses a Dynamic Delay DYN DEL [7:0] attribute which is used to further delay the DQS to accomplish the write leveling found in DDR3 memory. Write leveling is controlled by the DDR memory controller implementation. The DYN DELAY can set 128 possible delay step settings. In addition, the most significant bit will invert the clock for a 180-degree shift of the incoming clock. This will generate the DQSW signal used to generate the DQS output in the DQS output register block.

Figure 2-36 and Figure 2-37 show how the DQS transition signals that are routed to the PIOs.

Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on this topic.

Figure 2-38. LatticeECP3 Banks



LatticeECP3 devices contain two types of sysI/O buffer pairs.

1. **Top (Bank 0 and Bank 1) and Bottom sysIO Buffer Pairs (Single-Ended Outputs Only)**
   The sysI/O buffer pairs in the top banks of the device consist of two single-ended output drivers and two sets of single-ended input buffers (both ratioed and referenced). One of the referenced input buffers can also be configured as a differential input. Only the top edge buffers have a programmable PCI clamp.

   The two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

   The top and bottom sides are ideal for general purpose I/O, PCI, and inputs for LVDS (LVDS outputs are only allowed on the left and right sides). The top side can be used for the DDR3 ADDR/CMD signals.

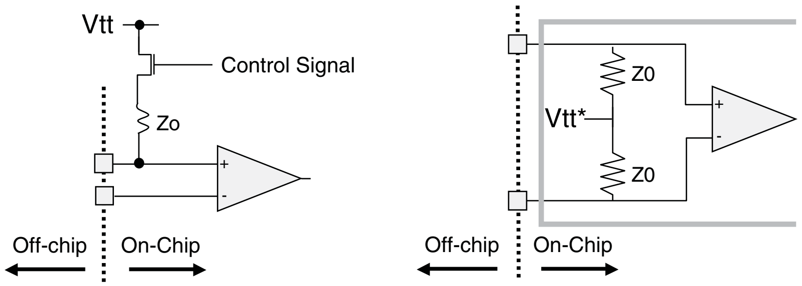
   The I/O pins located on the top and bottom sides of the device (labeled PTxxA/B or PBxxA/B) are fully hot socketable. Note that the pads in Banks 3, 6 and 8 are wrapped around the corner of the device. In these banks, only the pads located on the top or bottom of the device are hot socketable. The top and bottom side pads can be identified by the Lattice Diamond tool.

On-Chip Programmable Termination

The LatticeECP3 supports a variety of programmable on-chip terminations options, including:

- Dynamically switchable Single-Ended Termination with programmable resistor values of 40, 50, or 60 Ohms. External termination to Vtt should be used for DDR2 and DDR3 memory controller implementation.
- Common mode termination of 80, 100, 120 Ohms for differential inputs

Figure 2-39. On-Chip Termination



Programmable resistance (40, 50 and 60 Ohms)

*Vtt must be left floating for this termination

Parallel Single-Ended Input

Differential Input

See Table 2-12 for termination options for input modes.

Table 2-12. On-Chip Termination Options for Input Modes

IO_TYPE	TERMINATE to VTT[1, 2]	DIFFERENTIAL TERMINATION RESISTOR[1]
LVDS25	þ	80, 100, 120
BLVDS25	þ	80, 100, 120
MLVDS	þ	80, 100, 120
HSTL18_I	40, 50, 60	þ
HSTL18_II	40, 50, 60	þ
HSTL18D_I	40, 50, 60	þ
HSTL18D_II	40, 50, 60	þ
HSTL15_I	40, 50, 60	þ
HSTL15D_I	40, 50, 60	þ
SSTL25_I	40, 50, 60	þ
SSTL25_II	40, 50, 60	þ
SSTL25D_I	40, 50, 60	þ
SSTL25D_II	40, 50, 60	þ
SSTL18_I	40, 50, 60	þ
SSTL18_II	40, 50, 60	þ
SSTL18D_I	40, 50, 60	þ
SSTL18D_II	40, 50, 60	þ
SSTL15	40, 50, 60	þ
SSTL15D	40, 50, 60	þ

1. TERMINATE to VTT and DIFFRENTIAL TERMINATION RESISTOR when turned on can only have one setting per bank. Only left and right banks have this feature.
   Use of TERMINATE to VTT and DIFFRENTIAL TERMINATION RESISTOR are mutually exclusive in an I/O bank.
   On-chip termination tolerance +/– 20%
2. External termination to VTT should be used when implementing DDR2 and DDR3 memory controller.

LatticeECP3 Family Data Sheet
DC and Switching Characteristics

April 2014 **Data Sheet DS1021**

Absolute Maximum Ratings[1, 2, 3]

Supply Voltage V_{CC} . . . . –0.5 V to 1.32 V

Supply Voltage V_{CCAUX} . . . . –0.5 V to 3.75 V

Supply Voltage V_{CCJ} . . . . –0.5 V to 3.75 V

Output Supply Voltage V_{CCIO} . . . . –0.5 V to 3.75 V

Input or I/O Tristate Voltage Applied[4]. . . –0.5 V to 3.75 V

Storage Temperature (Ambient) . . . .–65 V to 150 °C

Junction Temperature (T_J) . . . .+125 °C

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.
4. Overshoot and undershoot of –2 V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

Recommended Operating Conditions[1]

Symbol	Parameter	Min.	Max.	Units
V_{CC}[2]	Core Supply Voltage	1.14	1.26	V
V_{CCAUX}[2, 4]	Auxiliary Supply Voltage, Terminating Resistor Switching Power Supply (SERDES)	3.135	3.465	V
V_{CCPLL}	PLL Supply Voltage	3.135	3.465	V
V_{CCIO}[2, 3]	I/O Driver Supply Voltage	1.14	3.465	V
V_{CCJ}[2]	Supply Voltage for IEEE 1149.1 Test Access Port	1.14	3.465	V
V_{REF1} and V_{REF2}	Input Reference Voltage	0.5	1.7	V
V_{TT}[5]	Termination Voltage	0.5	1.3125	V
t_{JCOM}	Junction Temperature, Commercial Operation	0	85	°C
t_{JIND}	Junction Temperature, Industrial Operation	-40	100	°C
SERDES External Power Supply[6]				
V_{CCIB}	Input Buffer Power Supply (1.2 V)	1.14	1.26	V
	Input Buffer Power Supply (1.5 V)	1.425	1.575	V
V_{CCOB}	Output Buffer Power Supply (1.2 V)	1.14	1.26	V
	Output Buffer Power Supply (1.5 V)	1.425	1.575	V
V_{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	1.14	1.26	V

1. For correct operation, all supplies except V_{REF} and V_{TT} must be held in their valid operation range. This is true independent of feature usage.
2. If V_{CCIO} or V_{CCJ} is set to 1.2 V, they must be connected to the same power supply as $V_{CC.}$ If V_{CCIO} or V_{CCJ} is set to 3.3 V, they must be connected to the same power supply as V_{CCAUX}.
3. See recommended voltages by I/O standard in subsequent table.
4. V_{CCAUX} ramp rate must not exceed 30 mV/µs during power-up when transitioning between 0 V and 3.3 V.
5. If not used, V_{TT} should be left floating.
6. See TN1176, LatticeECP3 SERDES/PCS Usage Guide for information on board considerations for SERDES power supplies.

Register-to-Register Performance[1, 2, 3]

Function	–8 Timing	Units
18x18 Multiply/Accumulate (Input & Output Registers)	200	MHz
18x18 Multiply-Add/Sub (All Registers)	400	MHz

1. These timing numbers were generated using ispLEVER tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.
3. For details on -9 speed grade devices, please contact your Lattice Sales Representative.

Derating Timing Tables

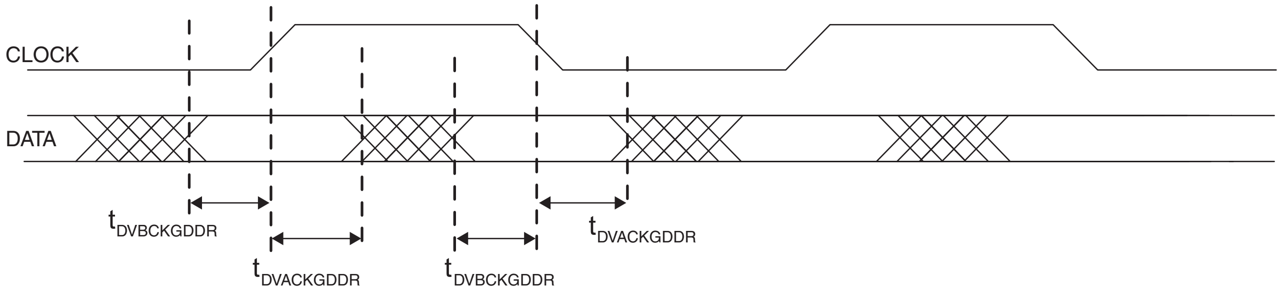
Logic timing provided in the following sections of this data sheet and the Diamond and ispLEVER design tools are worst case numbers in the operating range. Actual delays at nominal temperature and voltage for best case process, can be much better than the values given in the tables. The Diamond and ispLEVER design tools can provide logic timing numbers at a particular temperature and voltage.

LatticeECP3 External Switching Characteristics (Continued)[1, 2, 3, 13]

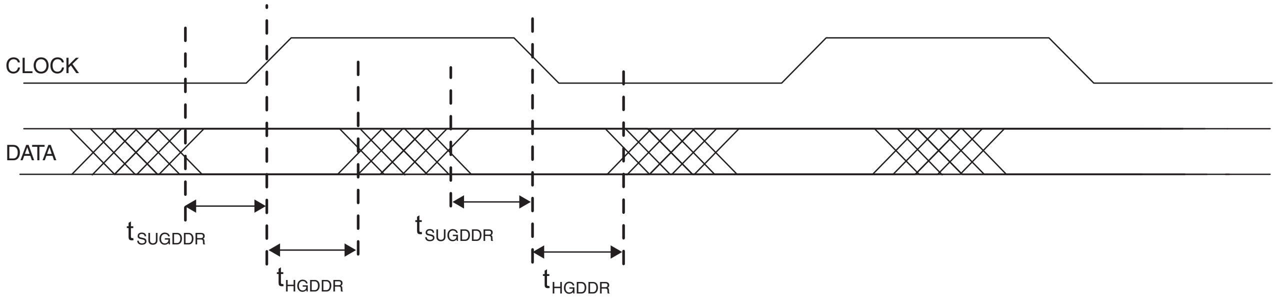
Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-150EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	—	3.8	—	4.2	—	4.6	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	ECP3-70EA/95EA	1.4	—	1.6	—	1.8	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-70EA/95EA	1.3	—	1.5	—	1.7	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-35EA	—	3.7	—	4.1	—	4.5	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	ECP3-35EA	1.2	—	1.4	—	1.6	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-35EA	1.3	—	1.4	—	1.5	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-35EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-17EA	—	3.5	—	3.9	—	4.3	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	ECP3-17EA	1.3	—	1.5	—	1.6	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-17EA	1.3	—	1.4	—	1.5	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-17EA	—	500	—	420	—	375	MHz
General I/O Pin Parameters Using Dedicated Clock Input Primary Clock with PLL with Clock Injection Removal Setting[2]									
t_{COPLL}	Clock to Output - PIO Output Register	ECP3-150EA	—	3.3	—	3.6	—	39	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.7	—	0.8	—	0.9	—	ns
t_{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-150EA	0.8	—	0.9	—	1.0	—	ns
t_{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.6	—	1.8	—	2.0	—	ns
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	—	0.0	—	0.0	—	0.0	ns
t_{COPLL}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	—	3.3	—	3.5	—	3.8	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.7	—	0.8	—	0.9	—	ns

Figure 3-8. Generic DDRX1/DDRX2 (With Clock Center on Data Window)



Transmit Parameters



Receive Parameters

LatticeECP3 Internal Switching Characteristics[1, 2, 5] (Continued)

Over Recommended Commercial Operating Conditions

Parameter	Description	–8		–7		–6		Units.
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{HWREN_EBR}	Hold Write/Read Enable to EBR Memory	0.141	—	0.145	—	0.149	—	ns
t_{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register	0.087	—	0.096	—	0.104	—	ns
t_{HCE_EBR}	Clock Enable Hold Time to EBR Output Register	–0.066	—	–0.080	—	–0.094	—	ns
t_{SUBE_EBR}	Byte Enable Set-Up Time to EBR Output Register	–0.071	—	–0.070	—	–0.068	—	ns
t_{HBE_EBR}	Byte Enable Hold Time to EBR Output Register	0.118	—	0.098	—	0.077	—	ns
DSP Block Timing[3]								
t_{SUI_DSP}	Input Register Setup Time	0.32	—	0.36	—	0.39	—	ns
t_{HI_DSP}	Input Register Hold Time	–0.17	—	–0.19	—	–0.21	—	ns
t_{SUP_DSP}	Pipeline Register Setup Time	2.23	—	2.30	—	2.37	—	ns
t_{HP_DSP}	Pipeline Register Hold Time	–1.02	—	–1.09	—	–1.15	—	ns
t_{SUO_DSP}	Output Register Setup Time	3.09	—	3.22	—	3.34	—	ns
t_{HO_DSP}	Output Register Hold Time	–1.67	—	–1.76	—	–1.84	—	ns
t_{COI_DSP}	Input Register Clock to Output Time	—	3.05	—	3.35	—	3.73	ns
t_{COP_DSP}	Pipeline Register Clock to Output Time	—	1.30	—	1.47	—	1.64	ns
t_{COO_DSP}	Output Register Clock to Output Time	—	0.58	—	0.60	—	0.62	ns
t_{SUOPT_DSP}	Opcode Register Setup Time	0.31	—	0.35	—	0.39	—	ns
t_{HOPT_DSP}	Opcode Register Hold Time	–0.20	—	–0.24	—	–0.27	—	ns
t_{SUDATA_DSP}	Cascade_data through ALU to Output Register Setup Time	1.69	—	1.94	—	2.14	—	ns
t_{HPDATA_DSP}	Cascade_data through ALU to Output Register Hold Time	–0.58	—	–0.80	—	–0.97	—	ns

1. Internal parameters are characterized but not tested on every device.
2. Commercial timing numbers are shown. Industrial timing numbers are typically slower and can be extracted from the Diamond or ispLEVER software.
3. DSP slice is configured in Multiply Add/Sub 18 x 18 mode.
4. The output register is in Flip-flop mode.
5. For details on –9 speed grade devices, please contact your Lattice Sales Representative.

LatticeECP3 Maximum I/O Buffer Speed (Continued)[1, 2, 3, 4, 5, 6]

Over Recommended Operating Conditions

Buffer	Description	Max.	Units
PCI33	PCI, V_{CCIO} = 3.3 V	66	MHz

1. These maximum speeds are characterized but not tested on every device.
2. Maximum I/O speed for differential output standards emulated with resistors depends on the layout.
3. LVCMOS timing is measured with the load specified in the Switching Test Conditions table of this document.
4. All speeds are measured at fast slew.
5. Actual system operation may vary depending on user logic implementation.
6. Maximum data rate equals 2 times the clock rate when utilizing DDR.

Serial Rapid I/O Type 2/CPRI LV E.24 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-15. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}[1]	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance		80	100	120	Ohms
J_{TX_DDJ}[3, 4, 5]	Output data deterministic jitter		—	—	0.17	UI
J_{TX_TJ}[2, 3, 4, 5]	Total output data jitter		—	—	0.35	UI

1. Rise and Fall times measured with board trace, connector and approximately 2.5pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
5. Values are measured at 2.5 Gbps.

Table 3-16. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 2.5 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 2.5 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J_{RX_DJ}[2, 3, 4, 5]	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
J_{RX_RJ}[2, 3, 4, 5]	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
J_{RX_SJ}[2, 3, 4, 5]	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
J_{RX_TJ}[1, 2, 3, 4, 5]	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.
2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

Pin Information Summary (Cont.)

Pin Information Summary		ECP3-95EA			ECP3-150EA	
Pin Type		484 fpBGA	672 fpBGA	1156 fpBGA	672 fpBGA	1156 fpBGA
Emulated Differential I/O per Bank	Bank 0	21	30	43	30	47
	Bank 1	18	24	39	24	43
	Bank 2	8	12	13	12	18
	Bank 3	20	23	33	23	37
	Bank 6	22	25	33	25	37
	Bank 7	11	16	18	16	24
	Bank 8	12	12	12	12	12
Highspeed Differential I/O per Bank	Bank 0	0	0	0	0	0
	Bank 1	0	0	0	0	0
	Bank 2	6	9	9	9	15
	Bank 3	9	12	16	12	21
	Bank 6	11	14	16	14	21
	Bank 7	9	12	13	12	18
	Bank 8	0	0	0	0	0
Total Single Ended/ Total Differential I/O per Bank	Bank 0	42/21	60/30	86/43	60/30	94/47
	Bank 1	36/18	48/24	78/39	48/24	86/43
	Bank 2	28/14	42/21	44/22	42/21	66/33
	Bank 3	58/29	71/35	98/49	71/35	116/58
	Bank 6	67/33	78/39	98/49	78/39	116/58
	Bank 7	40/20	56/28	62/31	56/28	84/42
	Bank 8	24/12	24/12	24/12	24/12	24/12
DDR Groups Bonded per Bank	Bank 0	3	5	7	5	7
	Bank 1	3	4	7	4	7
	Bank 2	2	3	3	3	4
	Bank 3	3	4	5	4	7
	Bank 6	4	4	5	4	7
	Bank 7	3	4	4	4	6
	Configuration Bank8	0	0	0	0	0
SERDES Quads		1	2	3	2	4

1.These pins must remain floating on the board.

LatticeECP3 Devices, Green and Lead-Free Packaging

The following devices may have associated errata. Specific devices with associated errata will be notated with a footnote.

Commercial

Part Number	Voltage	Grade	Power	Package[1]	Pins	Temp.	LUTs (K)
LFE3-17EA-6FTN256C	1.2 V	–6	STD	Lead-Free ftBGA	256	COM	17
LFE3-17EA-7FTN256C	1.2 V	–7	STD	Lead-Free ftBGA	256	COM	17
LFE3-17EA-8FTN256C	1.2 V	–8	STD	Lead-Free ftBGA	256	COM	17
LFE3-17EA-6LFTN256C	1.2 V	–6	LOW	Lead-Free ftBGA	256	COM	17
LFE3-17EA-7LFTN256C	1.2 V	–7	LOW	Lead-Free ftBGA	256	COM	17
LFE3-17EA-8LFTN256C	1.2 V	–8	LOW	Lead-Free ftBGA	256	COM	17
LFE3-17EA-6MG328C	1.2 V	–6	STD	Green csBGA	328	COM	17
LFE3-17EA-7MG328C	1.2 V	–7	STD	Green csBGA	328	COM	17
LFE3-17EA-8MG328C	1.2 V	–8	STD	Green csBGA	328	COM	17
LFE3-17EA-6LMG328C	1.2 V	–6	LOW	Green csBGA	328	COM	17
LFE3-17EA-7LMG328C	1.2 V	–7	LOW	Green csBGA	328	COM	17
LFE3-17EA-8LMG328C	1.2 V	–8	LOW	Green csBGA	328	COM	17
LFE3-17EA-6FN484C	1.2 V	–6	STD	Lead-Free fpBGA	484	COM	17
LFE3-17EA-7FN484C	1.2 V	–7	STD	Lead-Free fpBGA	484	COM	17
LFE3-17EA-8FN484C	1.2 V	–8	STD	Lead-Free fpBGA	484	COM	17
LFE3-17EA-6LFN484C	1.2 V	–6	LOW	Lead-Free fpBGA	484	COM	17
LFE3-17EA-7LFN484C	1.2 V	–7	LOW	Lead-Free fpBGA	484	COM	17
LFE3-17EA-8LFN484C	1.2 V	–8	LOW	Lead-Free fpBGA	484	COM	17

1. Green = Halogen free and lead free.

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-35EA-6FTN256C	1.2 V	–6	STD	Lead-Free ftBGA	256	COM	33
LFE3-35EA-7FTN256C	1.2 V	–7	STD	Lead-Free ftBGA	256	COM	33
LFE3-35EA-8FTN256C	1.2 V	–8	STD	Lead-Free ftBGA	256	COM	33
LFE3-35EA-6LFTN256C	1.2 V	–6	LOW	Lead-Free ftBGA	256	COM	33
LFE3-35EA-7LFTN256C	1.2 V	–7	LOW	Lead-Free ftBGA	256	COM	33
LFE3-35EA-8LFTN256C	1.2 V	–8	LOW	Lead-Free ftBGA	256	COM	33
LFE3-35EA-6FN484C	1.2 V	–6	STD	Lead-Free fpBGA	484	COM	33
LFE3-35EA-7FN484C	1.2 V	–7	STD	Lead-Free fpBGA	484	COM	33
LFE3-35EA-8FN484C	1.2 V	–8	STD	Lead-Free fpBGA	484	COM	33
LFE3-35EA-6LFN484C	1.2 V	–6	LOW	Lead-Free fpBGA	484	COM	33
LFE3-35EA-7LFN484C	1.2 V	–7	LOW	Lead-Free fpBGA	484	COM	33
LFE3-35EA-8LFN484C	1.2 V	–8	LOW	Lead-Free fpBGA	484	COM	33
LFE3-35EA-6FN672C	1.2 V	–6	STD	Lead-Free fpBGA	672	COM	33
LFE3-35EA-7FN672C	1.2 V	–7	STD	Lead-Free fpBGA	672	COM	33
LFE3-35EA-8FN672C	1.2 V	–8	STD	Lead-Free fpBGA	672	COM	33
LFE3-35EA-6LFN672C	1.2 V	–6	LOW	Lead-Free fpBGA	672	COM	33
LFE3-35EA-7LFN672C	1.2 V	–7	LOW	Lead-Free fpBGA	672	COM	33
LFE3-35EA-8LFN672C	1.2 V	–8	LOW	Lead-Free fpBGA	672	COM	33

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Date	Version	Section	Change Summary
March 2010	01.6	Architecture	Added Read-Before-Write information.
		DC and Switching Characteristics	Added footnote #6 to Maximum I/O Buffer Speed table.
			Corrected minimum operating conditions for input and output differential voltages in the Point-to-Point LVDS table.
		Pinout Information	Added pin information for the LatticeECP3-70EA and LatticeECP3-95EA devices.
		Ordering Information	Added ordering part numbers for the LatticeECP3-70EA and LatticeECP3-95EA devices.
			Removed dual mark information.
November 2009	01.5	Introduction	Updated Embedded SERDES features.
			Added SONET/SDH to Embedded SERDES protocols.
		Architecture	Updated Figure 2-4, General Purpose PLL Diagram.
			Updated SONET/SDH to SERDES and PCS protocols.
			Updated Table 2-13, SERDES Standard Support to include SONET/SDH and updated footnote 2.
		DC and Switching Characterisitcs	Added footnote to ESD Performance table.
			Updated SERDES Power Supply Requirements table and footnotes.
			Updated Maximum I/O Buffer Speed table.
			Updated Pin-to-Pin Peformance table.
			Updated sysCLOCK PLL Timing table.
			Updated DLL timing table.
			Updated High-Speed Data Transmitter tables.
			Updated High-Speed Data Receiver table.
			Updated footnote for Receiver Total Jitter Tolerance Specification table.
			Updated Periodic Receiver Jitter Tolerance Specification table.
			Updated SERDES External Reference Clock Specification table.
			Updated PCI Express Electrical and Timing AC and DC Characteristics.
			Deleted Reference Clock table for PCI Express Electrical and Timing AC and DC Characteristics.
			Updated SMPTE AC/DC Characteristics Transmit table.
			Updated Mini LVDS table.
			Updated RSDS table.
			Added Supply Current (Standby) table for EA devices.
			Updated Internal Switching Characteristics table.
			Updated Register-to-Register Performance table.
			Added HDMI Electrical and Timing Characteristics data.
			Updated Family Timing Adders table.
			Updated sysCONFIG Port Timing Specifications table.
			Updated Recommended Operating Conditions table.
			Updated Hot Socket Specifications table.
			Updated Single-Ended DC table.
			Updated TRLVDS table and figure.
			Updated Serial Data Input Specifications table.
			Updated HDMI Transmit and Receive table.
		Ordering Information	Added LFE3-150EA “TW” devices and footnotes to the Commercial and Industrial tables.

Date	Version	Section	Change Summary
			Updated Simplified Channel Block Diagram for SERDES/PCS Block diagram.
			Updated Device Configuration text section.
			Corrected software default value of MCCLK to be 2.5 MHz.
		DC and Switching Characteristics	Updated VCCOB Min/Max data in Recommended Operating Conditions table.
			Corrected footnote 2 in sysIO Recommended Operating Conditions table.
			Added added footnote 7 for t_{SKEW_PRIB} to External Switching Characteristics table.
			Added 2-to-1 Gearing text section and table.
			Updated External Reference Clock Specification (refclkp/refclkn) table.
			LatticeECP3 sysCONFIG Port Timing Specifications - updated t_{DINIT} information.
			Added sysCONFIG Port Timing waveform.
			Serial Input Data Specifications table, delete Typ data for $V_{RX-DIFF-S}$.
			Added footnote 4 to sysCLOCK PLL Timing table for t_{PFD}.
			Added SERDES/PCS Block Latency Breakdown table.
			External Reference Clock Specifications table, added footnote 4, add symbol name vREF-IN-DIFF.
			Added SERDES External Reference Clock Waveforms.
			Updated Serial Output Timing and Levels table.
			Pin-to-pin performance table, changed "typically 3% slower" to "typically slower".
			Updated timing information
			Updated SERDES minimum frequency.
			Added data to the following tables: External Switching Characteristics, Internal Switching Characteristics, Family Timing Adders, Maximum I/O Buffer Speed, DLL Timing, High Speed Data Transmitter, Channel Output Jitter, Typical Building Block Function Performance, Register-to-Register Performance, and Power Supply Requirements.
			Updated Serial Input Data Specifications table.
			Updated Transmit table, Serial Rapid I/O Type 2 Electrical and Timing Characteristics section.
		Pinout Information	Updated Signal Description tables.
			Updated Pin Information Summary tables and added footnote 1.
February 2009	01.0	—	Initial release.